

CZT3904 NPN
CZT3906 PNP

**SURFACE MOUNT
COMPLEMENTARY
SILICON TRANSISTORS**



SOT-223 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT3904, CZT3906 types are complementary silicon transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL	<u>CZT3904</u>	<u>CZT3906</u>	UNITS
Collector-Base Voltage	V_{CBO}	60	40	V
Collector-Emitter Voltage	V_{CEO}	40	40	V
Emitter-Base Voltage	V_{EBO}	6.0	5.0	V
Continuous Collector Current	I_C		200	mA
Power Dissipation	P_D		2.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}		62.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	<u>CZT3904</u>		<u>CZT3906</u>		UNITS
		MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$	-	50	-	50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60	-	40	-	V
BV_{CEO}	$I_C=1.0\text{mA}$	40	-	40	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	-	0.20	-	0.25	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.30	-	0.40	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.65	0.85	0.65	0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.95	-	0.95	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	40	-	60	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	70	-	80	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100	300	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	60	-	60	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	30	-	30	-	
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300	-	250	-	MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$	-	4.0	-	4.5	pF
C_{ib}	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	8.0	-	10	pF
h_{ie}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	1.0	10	2.0	12	k Ω

R5 (1-March 2010)

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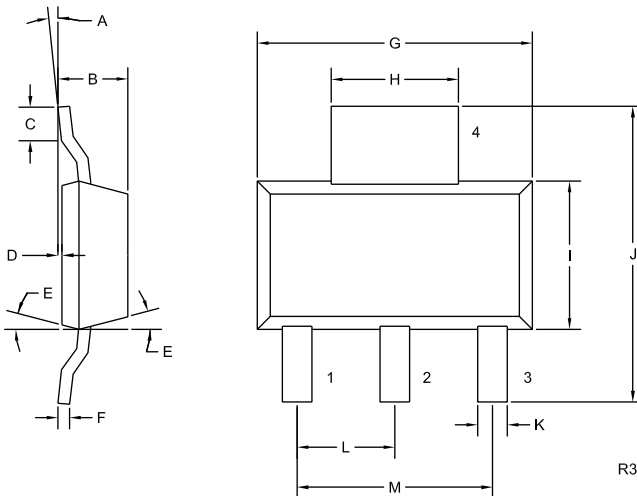
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	CZT3904		CZT3906		UNITS
		MIN	MAX	MIN	MAX	
h_{re}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	0.5	8.0	0.1	10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	100	400	100	400	
h_{oe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	1.0	40	3.0	60	μS
NF	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega$ $f=10\text{Hz to } 15.7\text{kHz}$	-	5.0	-	4.0	dB
t_d	$V_{CC}=3.0\text{V}, V_{BE}=0.5\text{V}, I_C=10\text{mA}, I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_r	$V_{CC}=3.0\text{V}, V_{BE}=0.5\text{V}, I_C=10\text{mA}, I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_s	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1.0\text{mA}$	-	200	-	225	ns
t_f	$V_{CC}=3.0\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1.0\text{mA}$	-	50	-	75	ns

SOT-223 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	10°	0°	10°
B	0.059	0.071	1.50	1.80
C	0.018	---	0.45	---
D	0.000	0.004	0.00	0.10
E	15°		15°	
F	0.009	0.014	0.23	0.35
G	0.248	0.264	6.30	6.70
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.70
J	0.264	0.287	6.70	7.30
K	0.024	0.033	0.60	0.85
L	0.091		2.30	
M	0.181		4.60	

SOT-223 (REV: R3)

LEAD CODE:

- 1) Base
- 2) Collector
- 3) Emitter
- 4) Collector

MARKING:

FULL PART NUMBER

R5 (1-March 2010)